Submitted with IDS of October 24, 2000

Page 5 of 11

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Form PTO-1449 U.S. Department of Commerce (Rev. 8-83)Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) Foreign Patent Document Number Document Number Date Country Class Subclass Translation Yes No 1-130131* 05/1989 JP			·					
(Rev. 8-83)Patent and Trademark Office INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) Filing Date: September 5, 2000 Group: 2871 FOREIGN PATENT DOCUMENTS Document Number Date Country Class Subclass Translation Yes No 1-130131* 05/1989 JP	Fr. 970.1449	U.S. Department of Commerce		Attorney Docket No. 0	756-2230	Serial No. 08/81	8,884	
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				Examiner Name	D. Nguyen
Sheet	1	of	1	Attorney Docket Number	0756-1653

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				Examiner Name	D. Nguyen
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